ON Semiconductor

Is Now



To learn more about onsemi™, please visit our website at www.onsemi.com

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application,

Type-C USB Port Protection Switch

Features

- Fully USB Data Port Protection
- V_{DD} 0 V 5.5 V (12 V DC tolerant)
- -18 V to +20 V DC Tolerance on HSD± Port
- ±25 V IEC 61000-4-5 Surge Protection w/o External TVS
- V_{DD} Operating Range, 2.7 V-5.5 V
- HSD RON: 5 Ω Typical
- C_{ON} = 5 pF Typical
- Wide -3 dB Bandwidth: > 720 MHz
- Low Power Operation: $I_{CC} < 10 \mu A$ (Typical)
- Over Voltage Protection: 3.6 V & 4.5 V

Typical Applications

- Smartphones
- Tablets
- Laptops

Safety Mechanisms Highlight

- 3.6 V & 4.5 V OVP Trip Point
- ±25 V Surge Protection without Need for External TVS

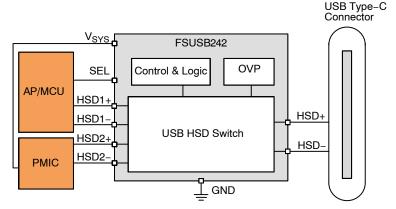


Figure 1. Application Schematic



ON Semiconductor®

www.onsemi.com



WLCSP9 1.20 × 1.20 CASE 567UL

MARKING DIAGRAM

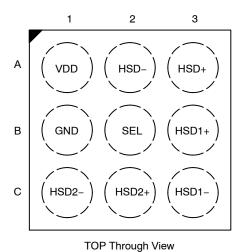


MT = Specific Device Code&K = 2 Digit Lot Run Code

X = Year

Y = 2 Week Data Code Z = Plant Code

PIN CONNECTION



ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

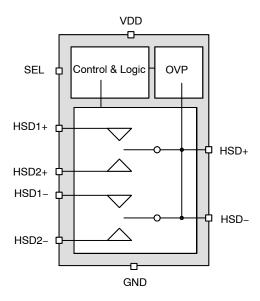


Figure 2. Simplified Block Diagram

Table 1. PIN FUNCTION DESCRIPTION

CSP Bump	Name	Туре	Description	
A1	VDD	Power	Supply Power	
B1	GND	Ground	Ground	
A3	HSD+	Data	Common High Speed Data Bus	
A2	HSD-	Data	Common High Speed Data Bus	
B3	HSD1+	Data	Multiplexed High Speed Data Port 1	
СЗ	HSD1-	Data	Multiplexed High Speed Data Port 1	
C2	HSD2+	Data	Multiplexed High Speed Data Port 2	
C1	HSD2-	Data	Multiplexed High Speed Data Port 2	
B2	SEL	I/O	Tri-Input HSD Switch Select & /OE	

Table 2. SWITCH TRUTH TABLE CONFIGURATION

VDD	SEL	Switch Configuration
UVLO	X Switch off High impedance	
Valid	0 HSD+ = HSD1+, HSD- = HSD1-	
Valid	1	HSD+ = HSD2+, HSD- = HSD2-
Valid	Float/High-Z	Switch Disable High impedance

APPLICATION INFORMATION

Over Voltage Protection

Over voltage protection turns the switch off if the inputs HSD+/HSD- rise above the over voltage trip threshold.

Under Voltage Lockout

The under-voltage lockout on V_{DD} pin turns the switch off if the V_{DD} voltage drops below the lockout threshold. With the SELpin active, the input voltage rising above the UVLO threshold releases the lockout and enables the switch.

Tri-State Input Control Pin (SEL)

The SEL pin can be tri-stated to disable the switch to save power, there are a few ways to achieve this. If the SEL pin is controlled by GPIO in the system, if the GPIO pin has a High-Z state where the impedance of the High-Z state is

larger then 2.5 M Ω the switch will recognize the High–Z state and disable the switch. If the system does not have GPIO that supports High–Z state, the user can utilize 2 MOSFETs or a Logic Device to achieve the same result.

For GPIO

The SEL pin function below:

- If the input is pulled up with less than 50 k Ω it will be considered as Logic High
- If the input is pulled down with less than 50 kΩ it will be consider as Logic Low
- If the input is pulled up or down with more 2.5 M Ω it will be consider as float/High-Z

System Timing Diagram

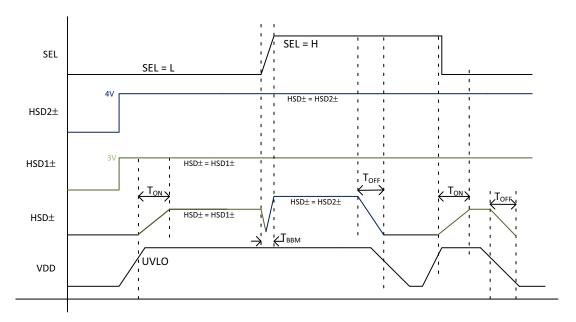


Figure 3. System Timing Plot

System Block Diagrams

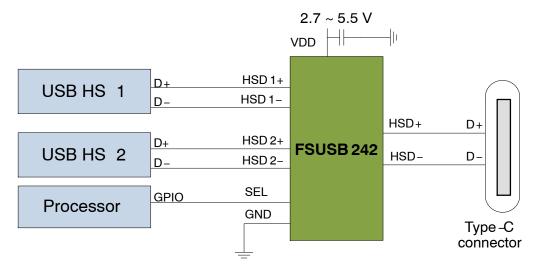


Figure 4. Application of 2x USB HS interface

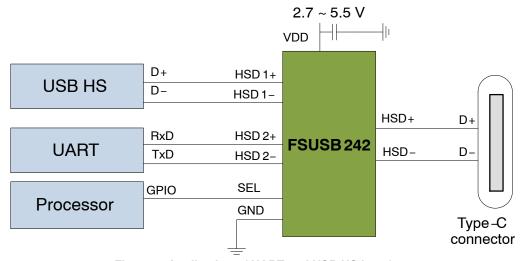


Figure 5. Application of UART and USB HS interface

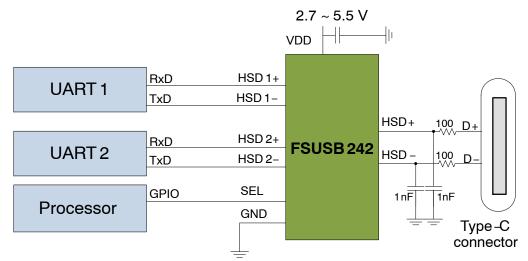


Figure 6. Application of 2x UART interface

When 2x UART signals are switched over FSUSB242, both 100 ohm series resistor and 1 nF bypass capacitors are recommended in the common switch path as above. If FSUSB242 is used to switch USB and UART signals, connect UART signals to HSD1.

USB High Speed Eye Diagram

$V_{DD} = 5.5 \ V \ HSD \ to \ HSD1 \ Path$

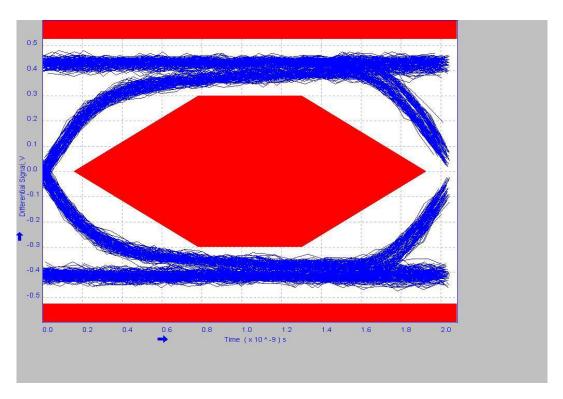


Figure 7. HS USB Eye @ V_{DD} = 5 V

 $V_{DD} = 2.7 \ V \ HSD \ to \ HSD2 \ Path$

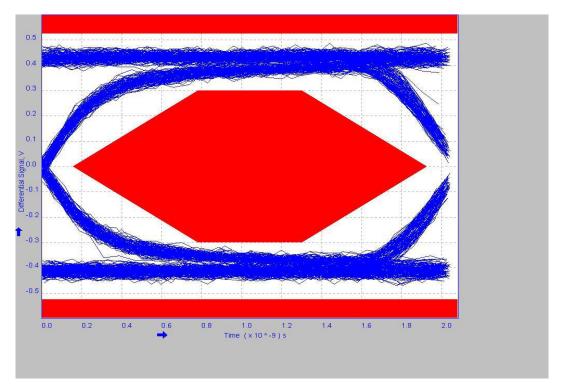


Figure 8. HS USB Eye @ V_{DD} = 2.7 V

Table 3. ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Min	Max	Unit
V_{DD}	Supply Voltage from V _{DD}			-0.5	12.0	V
V_{SW}	DC Input voltage tolerance for HSD±, to GND			-18	20	V
	DC Input voltage tolerance for HSD1±, HSD2± to GND			-1.2	6	V
V _{CONTROL}	DC Input Voltage (SEL)			-0.5	6	V
I _{SW}	DC HSD Switch Current				100	mA
I _{IK}	DC Input Diode Current	DC Input Diode Current				mA
T _{STORAGE}	Storage Temperature Range			-65	+150	°C
TJ	Maximum Junction Temperature				+150	°C
TL	Lead Temperature (Soldering, 10 secon	ad Temperature (Soldering, 10 seconds)			+260	°C
ESD	IEC 61000-4-2 System ESD (Note 1)	Connector Pins (HSD±)	Air Gap	15		kV
			Contact	8		1
	Human Body Model, JEDEC	Power to GND	•	2		kV
	JESD22-A114	Internal Pin to GND (HSD1±, HSD2±)		2		
		External Pin to GND (HSD±)		14		
	Charged Device Model, JEDEC All Pins LESD22–C101		1			
	IEC 61000-4-5 Surge Protection	HSD±, to GND		±25		٧
		V _{DD} to GND		+12		V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
V _{DD}	Supply Voltage	2.7	4.2	5.5	V
V _{SW1}	HSD1 Switch I/O Signal Swing Voltage (Note 2)	-0.5		3.6	V
V _{SW2}	HSD2 Switch I/O Signal Swing Voltage (Note 2)	-0.5		4.5	V
I _{CCSW}	Maximum HSD Switch Continuous Current			75	mA
V _{CNTRL}	Control Input Voltage (SEL)	-0.5		V_{DD}	V
T _A	Operating Temperature	-40		+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 5. DC ELECTRICAL CHARACTERISTICS

(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at $T_A = 25^{\circ}$ C and $V_{DD} = 4.2 \text{ V}$ unless otherwise specified.)

				T _A = -40 to +85°C T _J = -40 to +125°C			
Symbol	Characteristic	V _{DD} (V)	Conditions	Min	Тур	Max	Unit
BASIC OPERATION DEVICE							
I _{CC}	Quiescent Supply Current	2.7 to 5.5	WLCSP: /OE = H & L, I _{OUT} = 0		10		μΑ
I _{OFF}	Power-Off Leakage Current	0	V _{SWHSD1} = 0 V to 3.6 V, V _{SWHSD2} = 0 V to 4.5 V	-3		3	μΑ

^{1.} System level test that depends on end system for actual performance. These tests results are with external TVS protection. These specs are listed as general guidelines for expected performance in actual system and do not guarantee listed performance.

^{2.} The switch swing voltage is based on the OVP trip level, and when OVP triggers the switch will be disabled to protect the host and no longer in the standard operating condition, once over voltage is removed the device will automatically recover back to normal condition.

Table 5. DC ELECTRICAL CHARACTERISTICS (continued)

(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at $T_A = 25^{\circ}C$ and $V_{DD} = 4.2 \text{ V}$ unless otherwise specified.)

			T _A = -40 to +85°C T _J = -40 to +125°C				
Symbol	Characteristic	V _{DD} (V)	Conditions	Min	Тур	Max	Unit
BASIC OPERA	TION DEVICE						
I _{IN}	Control Input Leakage	2.7 to 5.5	V _{CNTRL} = 0 V to V _{DD}	-2		4	μА
l _{OZ}	Off State Leakage	2.7 to 5.5	HSD± ≥ 0 V, HSD1±, HSD2± ≤ 3.6 V	-3		5	μΑ
BASIC OPERA	TION HSD SWITCH					•	
R _{ON}	HSD Path On Resistance	2.7 to 5.5	I _{OUT} = 8 mA, V _{SW} = 0 V to 0.4 V		5		Ω
$\Delta R_{ extsf{ON}}$	HSD Path Delta R _{ON}	2.7 to 5.5	I _{OUT} = 8 mA, V _{SW} = 0 V to 0.4 V		0.15		Ω
V _{IH}	SEL Input Voltage High	2.7 to 5.5		1.3			V
V_{IM}	SEL Input Voltage Middle (Note 3)	2.7 to 5.5		0.8		1.0	٧
V _{IL}	SEL Input Voltage Low	2.7 to 5.5				0.5	V
Zfloat	Impedance to VDD or GND detected as a Float including VDD = 0	2.7 to 5.5		2.5			МΩ
1	Input OVP Lockout for HSD1 (FSUSB242UCX)	2.7 to 5.5	V _{HSD±} Rising, SEL = 0	3.6	3.8	4.0	V
			V _{HSD±} Falling, SEL = 0	3.3	3.5		
	Input OVP Lockout for HSD1 (FSUSB242UCXF45)	2.7 to 5.5	V _{HSD±} Rising, SEL = 0	4.5	4.7	4.9	V
			V _{HSD±} Falling, SEL = 0	4.2	4.4		
V _{OV_TRIP2}	nput OVP Lockout for HSD2	2.7 to 5.5	V _{HSD±} Rising, SEL = 1	4.5	4.7	4.9	V
	11002		V _{HSD±} Falling, SEL = 1	4.2	4.4		1
V _{OV TRIP3 F45}	Input OVP Lockout for both HSD1 and HSD2	2.7 to 5.5	V _{HSD±} Rising	4.5	4.7	4.9	V
(14010 4)	TIOD I did TIOD2		V _{HSD±} Falling	4.2	4.4		1
V _{OV_HYS}	Input OVP Hysteresis	2.7 to 5.5			0.3		V
V _{NV_TRIP}	Input Negative Voltage	2.7 to 5.5	V _{HSD±} Falling		-1.0		V
	Lockout		V _{HSD±} Rising		-0.7		
V _{NV_HYS}	Input OVP Hysteresis	2.7 to 5.5			0.3		V
V _{CL}	Clamping Voltage	2.7 to 5.5	$V_{HSD\pm} \ge V_{OV_TRIP}$		4.5		V
V _{UVLO}	Under-Voltage Lockout		V _{DD} Rising		2.4	2.7	V
			V _{DD} Falling		2.3		1
TSD	Thermal Shutdown (Note 3)		Shutdown Threshold		150		°C
			Return from Shutdown		130		
			Hysteresis		20		1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Guaranteed by characterization or Design, not production tested.

4. FSUSB242F45UCX OVP threshold.

Table 6. AC ELECTRICAL CHARACTERISTICS

(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at T_A = 25°C and V_{DD} = 4.2 V unless otherwise specified.)

				$T_A = -40 \text{ to } +85^{\circ}\text{C}$ $T_J = -40 \text{ to } +125^{\circ}\text{C}$		T _A = -40 to +85°C T _J = -40 to +125°C	
Symbol	Characteristic	V _{DD} (V)	Conditions	Min	Тур	Max	Unit
HSD SWIT	CH TIMING PARAMETER						
t _{OVP}	OVP Response Time (Note 53)	2.7 to 5.5	I_{OUT} = 8 mA, C_L = 5 pF, R_L = 50 Ω , $V_{HSD\pm}$ = 3.3 V to 4.9 V		0.35		μs
t _{ON}	Turn-On Time, SEL to Output	2.7 to 5.5	R_L = 50 Ω , C_L = 5 pF		0.1		ms
t _{OFF}	Turn-Off Time, SEL to Output	2.7 to 5.5	$\begin{aligned} R_L &= 50 \ \Omega, \ C_L = 5 \ pF, \\ V_{SW} &= 0.8 \ V \end{aligned}$		0.2		μs
t _{PD}	Propagation Delay (Note 5)	2.7 to 5.5	$R_L = 50 \Omega$, $C_L = 5 pF$, $V_{SW} = 0.8 V$		1.3		ns
t _{BBM}	Break-Before-Make (Note 5)	2.7 to 5.5	$R_L = 50 \Omega, C_L = 5 pF, V_{SW1} = V_{SW2} = 0.8 V$		50		μs
t _{SK(P)}	Skew of Opposite Transitions of the Same Output (Note 5)	2.7 to 5.5	V_{SW} = 0.2 Vdiff _{PP} , R_L = 50 Ω , C_L = 5 pF		35		ps
tı	Total Jitter (Note 5)	2.7 to 5.5	$\begin{array}{c} V_{SW} = 0.2 \ V diff_{PP}, \ R_L = 50 \ \Omega, \\ C_L = 5 \ pF, \ t_R = t_F = 500 \ ps \\ (10-90\%) \ @ \ 480 \ Mbps \\ (PRBS = 2^{15} - 1) \end{array}$		250		ps
HSD± SWI	TCH CAPACITANCE						
C _{IN}	Control Pin Input Capacitance (Note 5)	0			1.5		pF
C _{ON}	HSD± On Capacitance (Note 5)	2.7 to 5.5	SEL = L/H, f = 240 MHz		4		
C _{OFF}	HSD± Off Capacitance (Note 5)	2.7 to 5.5	SEL = Float, f = 240 MHz		3		
HSD SWIT	CH BANDWIDTH						
BW	-3dB SDD21 Bandwidth	2.7 to 5.5	$R_L = 50 \Omega$, $C_L = 0 pF$		1000		MHz
	(Note 5)		R _L = 50 Ω, C _L = 5 pF		550		MHz
HSD SWIT	CH AC PARAMETER						
O _{IRR}	Off Isolation (Note 5)	2.7 to 5.5	R _L = 50 Ω, f = 240 MHz		-35		dB
Xtalk	Non-Adjacent Channel Crosstalk (Note 5)	2.7 to 5.5	R _L = 50 Ω, f = 240 MHz		-40		dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Guaranteed by characterization or Design, not production tested.

TEST DIAGRAMS

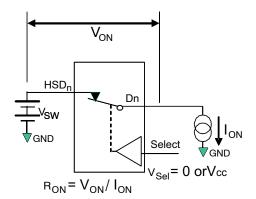
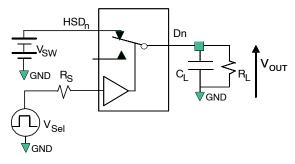


Figure 9. On Resistance



 R_L , R_S , and C_L are functions of the application environment (see AC Tables for specific values) C_L includes test fixture and stray capacitance.

Figure 11. AC Test Circuit Load

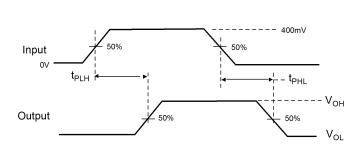
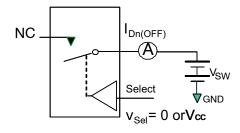


Figure 13. Propagation Delay (t_Rt_F - 500 ps)



**Each switch port is tested separately

Figure 10. Off Leakage

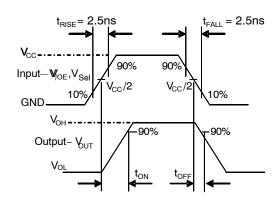


Figure 12. Turn-On / Turn-Off Waveforms

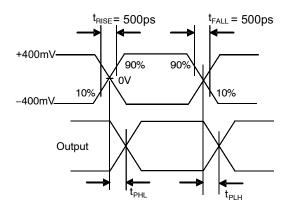


Figure 14. Intra-Pair Skew Test t_{SK(P)}

TEST DIAGRAMS (Continued)

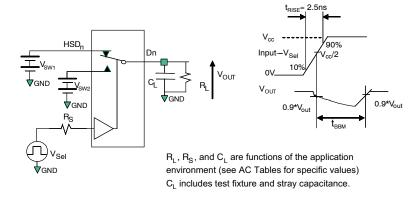


Figure 15. Break-Before-Make Interval Timing

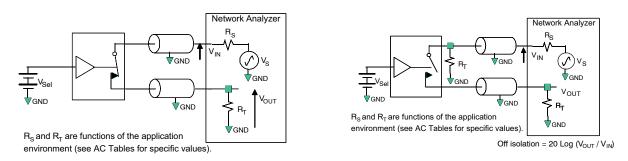


Figure 16. Bandwidth

Figure 17. Channel Off Isolation

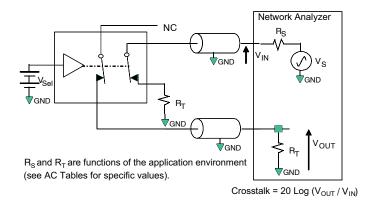
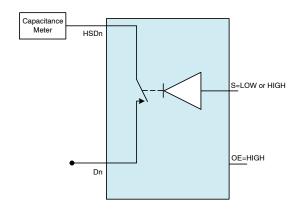


Figure 18. Non-Adjacent Channel-to-Channel Crosstalk

TEST DIAGRAMS (Continued)



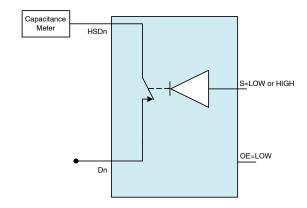


Figure 19. Channel Off Capacitance

Figure 20. Channel On Capacitance

ORDERING INFORMATION

Table 7. AVAILABLE PART NUMBERS

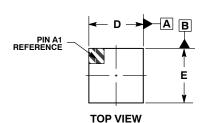
Part Number	Device Code	Operating Temperature Range	Package	Packing Method†
FSUSB242UCX	MT	−40 to 85°C	9-Ball WLCSP (1.20 x 1.20 mm)	Tape and Reel
FSUSB242F45UCX	MU	−40 to 85°C	9-Ball WLCSP (1.20 x 1.20 mm)	Tape and Reel

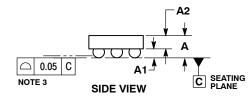
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

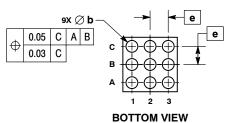


WLCSP9, 1.2x1.2x0.48 CASE 567UL **ISSUE A**

DATE 07 JUL 2017





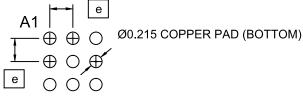


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS.
 COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE SOLDER BALLS.

	MILLIMETERS					
DIM	MIN NOM MAX					
Α	0.450	0.488	0.526			
A1	0.176	0.196	0.216			
A2	0.274	0.292	0.310			
b	0.24	0.26	0.28			
D	1.14	1.20	1.26			
E	1.14	1.20	1.26			
e		0.40 BSC	;			

RECOMMENDED SOLDERING FOOTPRINT* (NSMD PAD TYPE)



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON64604G	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	WLCSP9, 1.2x1.2x0.48		PAGE 1 OF 1		

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative